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60 V, single N-channel Trench MOSFET

6 August 2015

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protected

3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | - | 60 | V |
| V_{GS} | gate-source voltage | | | -20 | - | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{sp} = 25 °C | | - | - | 300 | mA |
| | | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | - | 190 | mA |
| Static chara | cteristics | | ' | | ' | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 10 V; I_D = 100 mA; T_j = 25 °C | | - | 3 | 4.5 | Ω |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².





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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1 | G | gate | <u></u> 3 | D I |
| 2 | S | source | | |
| 3 | D | drain | TO-236AB (SOT23) | G S 017aaa255 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|----------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| NX7002AK | TO-236AB | plastic surface-mounted package; 3 leads | SOT23 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code [1] |
|-------------|------------------|
| NX7002AK | %CM |

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 60 | V |
| V_{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{sp} = 25 °C | | - | 300 | mA |
| | | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | 190 | mA |
| | | V _{GS} = 10 V; T _{amb} = 100 °C | [1] | - | 120 | mA |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | | - | 760 | mA |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 265 | mW |
| | | | [1] | - | 325 | mW |
| | | T _{sp} = 25 °C | | - | 1330 | mW |
| T _j | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-dra | in diode | | 1 | | 1 | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | 190 | mA |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

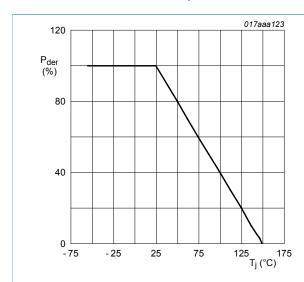


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

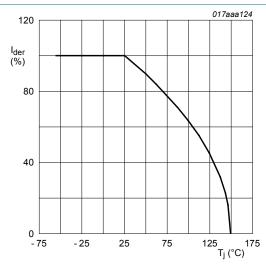


Fig. 2. Normalized continuous drain current as a function of junction temperature

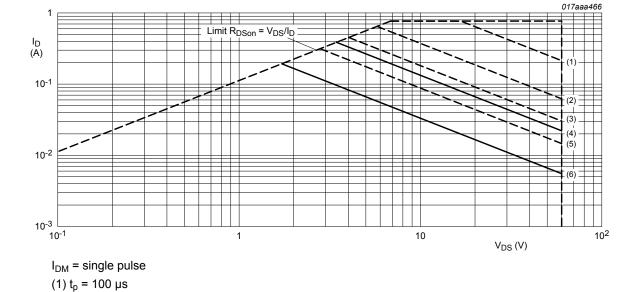
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100~\%$$

NX7002AK

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(2) $t_p = 1 \text{ ms}$

(3) $t_p = 10 \text{ ms}$

(4) DC; T_{sp} = 25 °C

 $(5) t_p = 100 \text{ ms}$

(6) DC; T_{amb} = 25 °C; drain mounting pad 1 cm²

Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | | [1] | - | 410 | 470 | K/W |
| | | | [2] | - | 330 | 380 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 95 | K/W |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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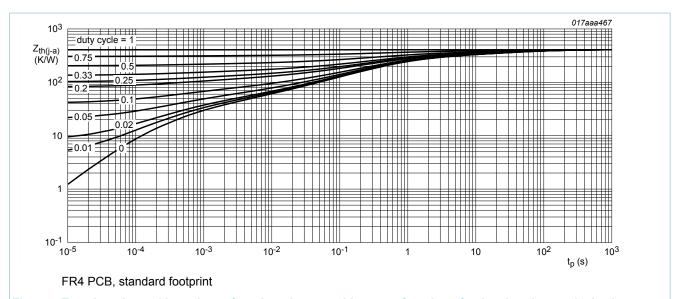


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

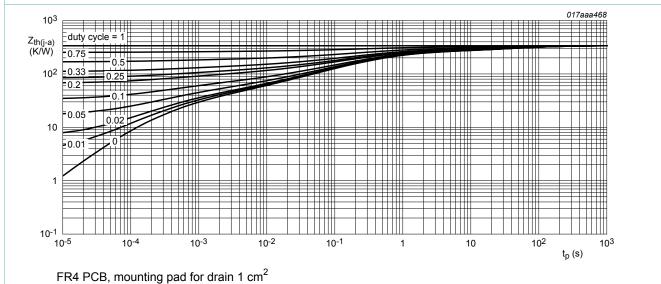


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

Product data sheet

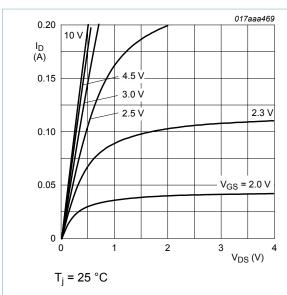
60 V, single N-channel Trench MOSFET

10. Characteristics

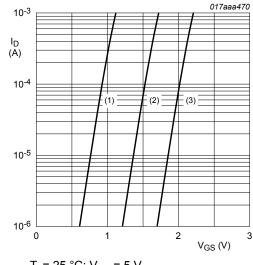
Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|-----------------------------------|--|------|------|------|------|
| Static char | racteristics | | ' | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 60 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 1.1 | 1.6 | 2.1 | V |
| I _{DSS} | drain leakage current | V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C | - | - | 1 | μΑ |
| | | V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C | - | - | 10 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 2 | μΑ |
| | | V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -2 | μΑ |
| | | V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 0.5 | μA |
| | | V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -0.5 | μA |
| | | V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| | | V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -100 | nA |
| Boon | drain-source on-state resistance | V_{GS} = 10 V; I_D = 100 mA; T_j = 25 °C | - | 3 | 4.5 | Ω |
| | | V _{GS} = 10 V; I _D = 100 mA; T _j = 150 °C | - | 6.2 | 9.2 | Ω |
| | | V _{GS} = 5 V; I _D = 100 mA; T _j = 25 °C | - | 3.7 | 5.2 | Ω |
| g _{fs} | forward transconductance | V_{DS} = 10 V; I_{D} = 200 mA; T_{j} = 25 °C | - | 500 | - | mS |
| Dynamic c | haracteristics | | , | | | |
| Q _{G(tot)} | total gate charge | V_{DS} = 30 V; I_{D} = 200 mA; V_{GS} = 4.5 V; | - | 0.33 | 0.43 | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C | - | 0.12 | - | nC |
| Q_{GD} | gate-drain charge | | - | 0.09 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V; | - | 15 | 20 | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 3.4 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 2 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 40 V; R_L = 250 Ω ; V_{GS} = 10 V; | - | 6 | 12 | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$ | - | 7 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 11 | 20 | ns |
| t _f | fall time | | - | 5 | - | ns |
| Source-dra | ain diode | | 1 | 1 | -1 | |
| V_{SD} | source-drain voltage | I _S = 115 mA; V _{GS} = 0 V; T _i = 25 °C | 0.47 | 0.8 | 1.2 | V |

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Output characteristics: drain current as a Fig. 6. function of drain-source voltage; typical values



$$T_i = 25 \,^{\circ}C; V_{DS} = 5 \,^{\circ}V$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Sub-threshold drain current as a function of Fig. 7. gate-source voltage

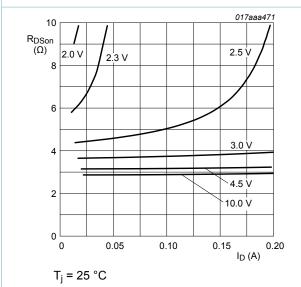
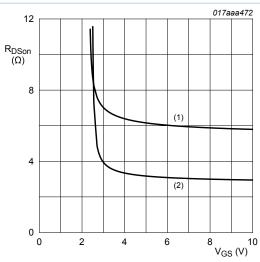


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 0.2 A$

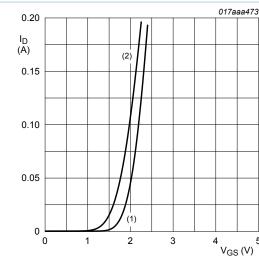
(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_D \times R_{DSon}$ (1) $T_j = 25 \, ^{\circ}C$

(2) $T_i = 150 \, ^{\circ}C$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

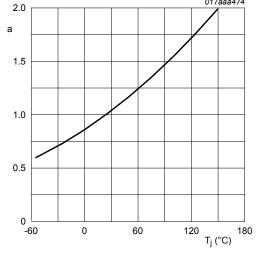
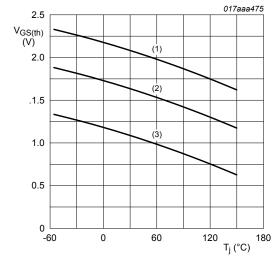


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

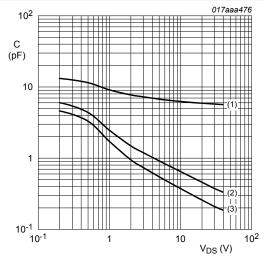
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 I_D = 0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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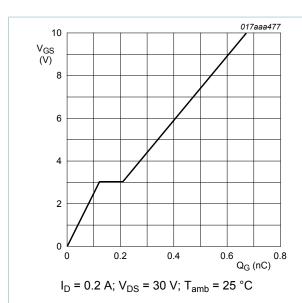


Fig. 14. Gate-source voltage as a function of gate charge; typical values

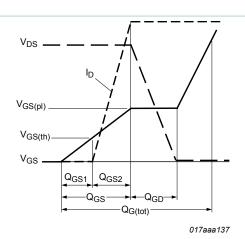
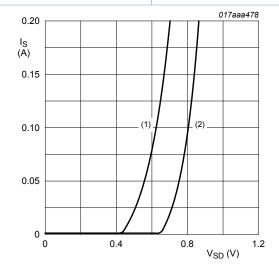


Fig. 15. MOSFET transistor: Gate charge waveform definitions



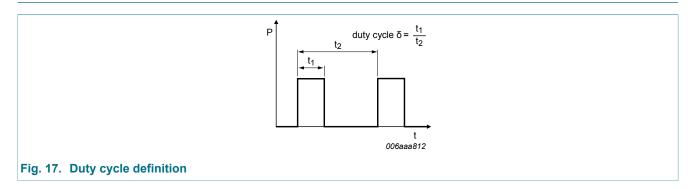
 $V_{GS} = 0 V$ (1) $T_j = 150 \,^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 16. Source current as a function of source-drain voltage; typical values

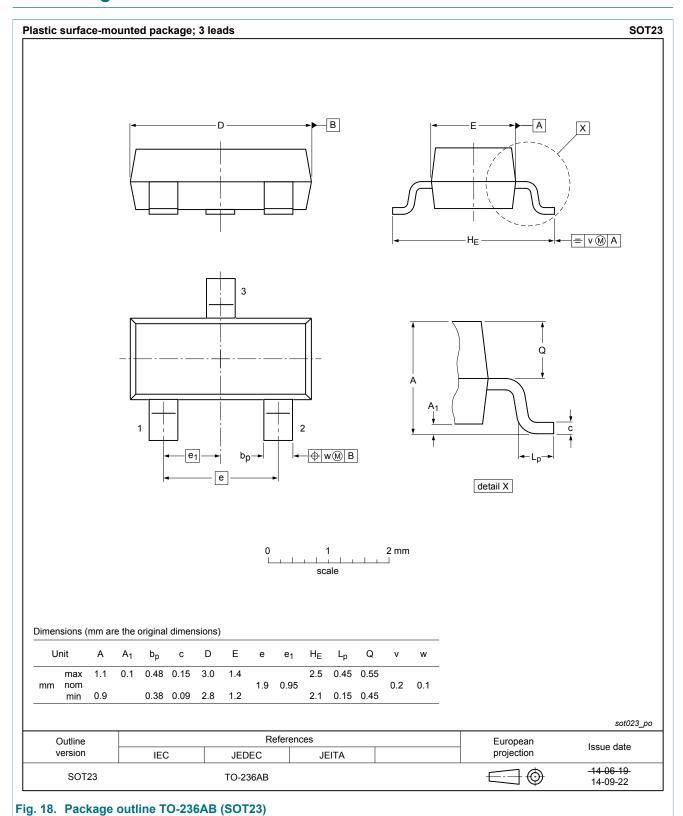
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11. Test information



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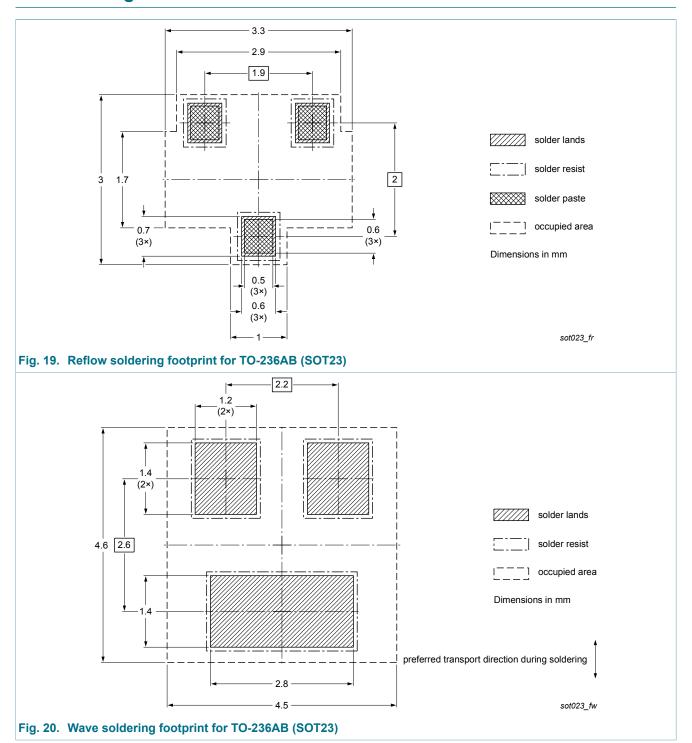
12. Package outline



Product data sheet

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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|---------------|--------------------|---------------|--------------|
| NX7002AK v.7 | 20150806 | Product data sheet | - | NX7002AK v.6 |
| Modifications: | Dynamic parar | meters updated | | , |
| NX7002AK v.6 | 20150521 | Product data sheet | - | NX7002AK v.5 |
| NX7002AK v.5 | 20130213 | Product data sheet | - | NX7002AK v.4 |
| NX7002AK v.4 | 20121213 | Product data sheet | - | NX7002AK v.3 |
| NX7002AK v.3 | 20120710 | Product data sheet | - | NX7002AK v.2 |
| NX7002AK v.2 | 20120301 | Product data sheet | - | NX7002AK v.1 |
| NX7002AK v.1 | 20120212 | Product data sheet | - | - |

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15. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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